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Formation of $Ge_{35}In_8S_{57}$ amorphous films for optical applications

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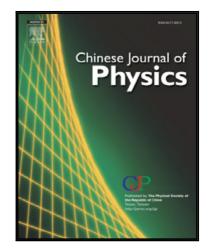
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Highlights

- Study the structure, optical and electrical properties of $Ge_{35}In_8S_{57}$ with different film thickness.
- Structural investigations of $Ge_{35}In_8S_{57}$ system have been studied.
- The linear and nonlinear studies have been studied for these films.
- The third order nonlinear optical susceptibility of the present system is calculated.

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